



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

3LP01SS — General-Purpose Switching Device Applications

Features

- Low ON-resistance
- High-speed switching
- 2.5V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		-30	V
Gate-to-Source Voltage	V_{GS}		±10	V
Drain Current (DC)	I_D		-0.1	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	-0.4	A
Allowable Power Dissipation	P_D		0.15	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

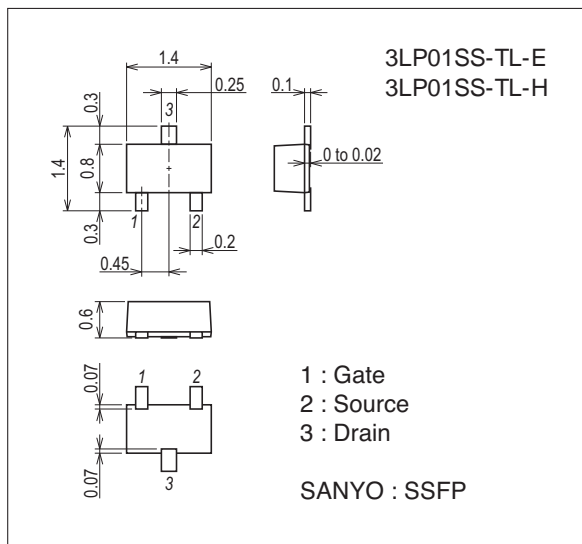
This product is designed to "ESD immunity < 200V**", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ)

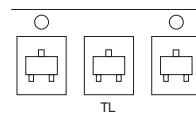
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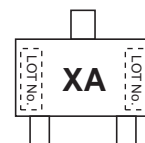
Product & Package Information

- Package : SSFP
- JEITA, JEDEC : SC-81
- Minimum Packing Quantity : 8,000 pcs./reel

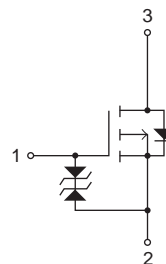
Packing Type: TL



Marking



Electrical Connection



SANYO Semiconductor Co., Ltd.

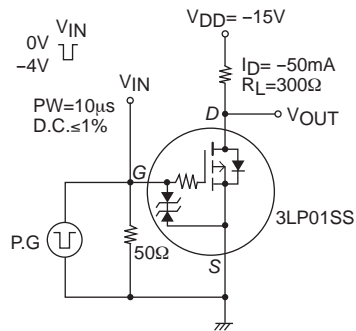
<http://semicon.sanyo.com/en/network>

3LP01SS

Electrical Characteristics at Ta=25°C

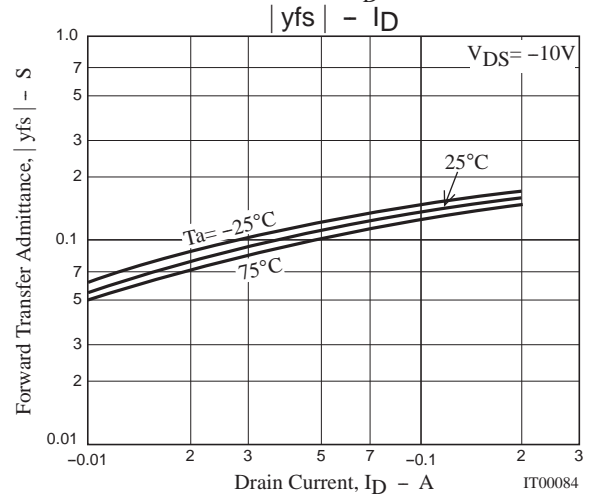
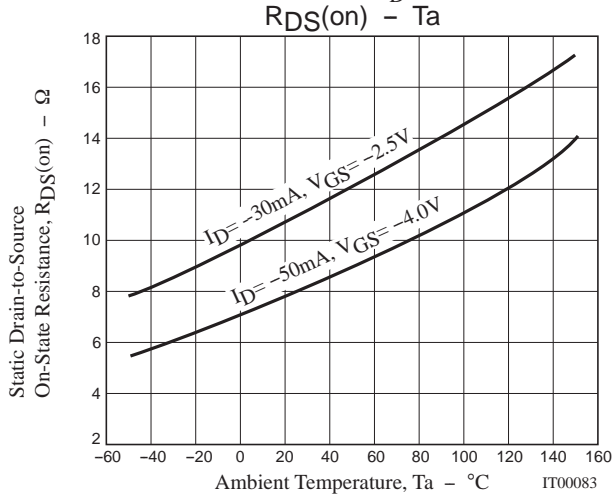
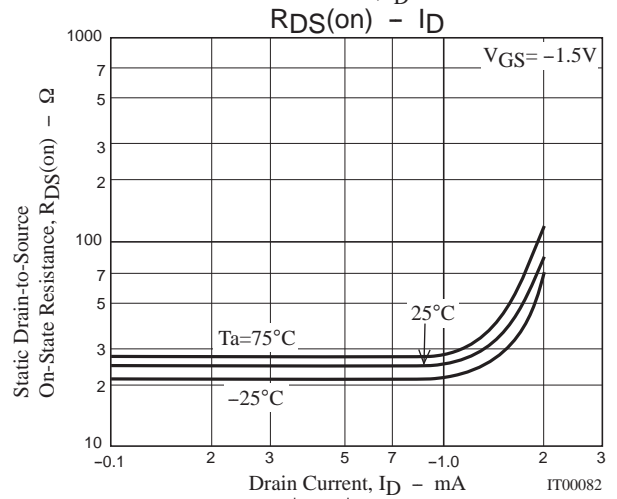
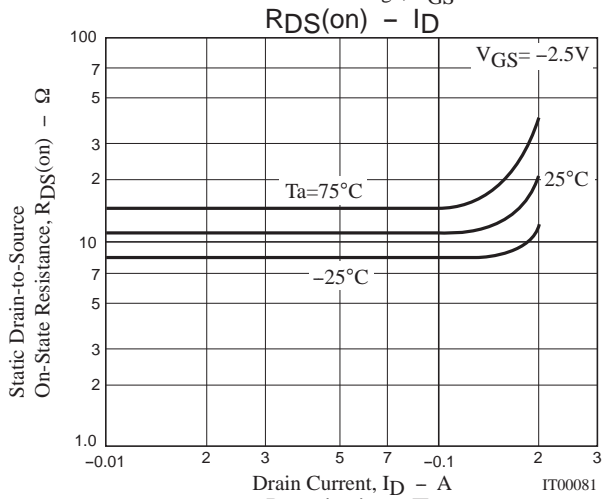
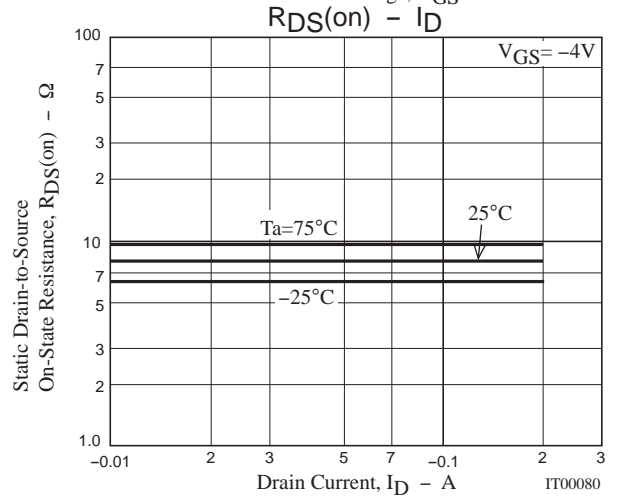
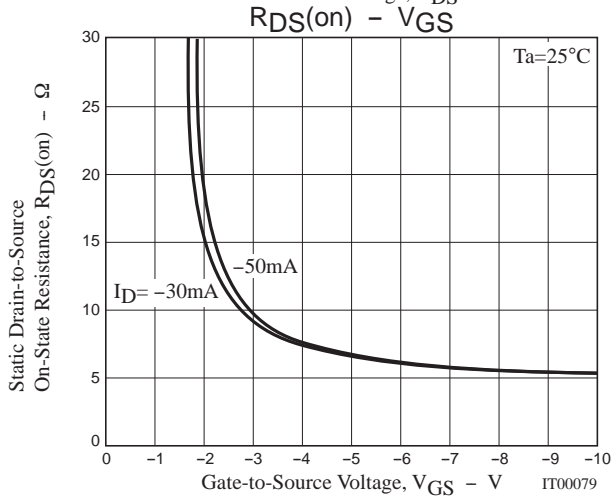
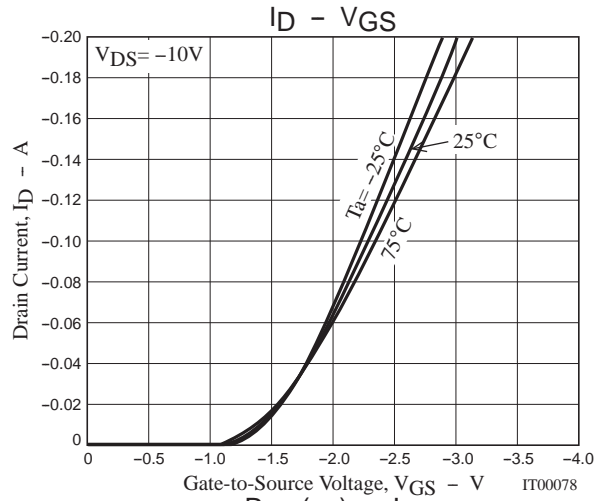
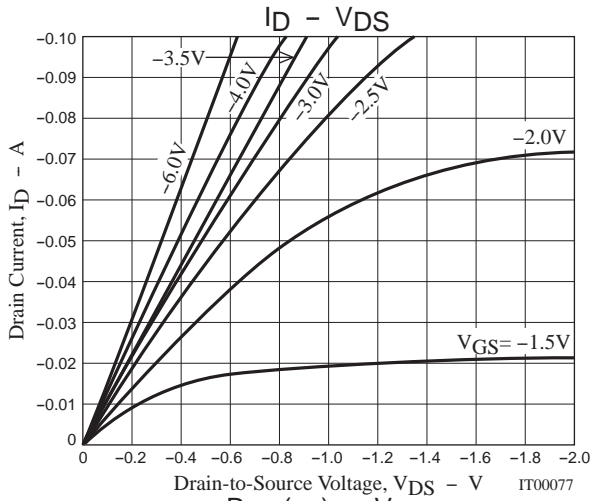
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}$, $V_{GS}=0\text{V}$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{V}$, $V_{GS}=0\text{V}$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8\text{V}$, $V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}$, $I_D = -100\mu\text{A}$	-0.4		-1.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10\text{V}$, $I_D = -50\text{mA}$	80	110		mS
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -50\text{mA}$, $V_{GS} = -4\text{V}$		8	10.4	Ω
	$R_{DS(on)2}$	$I_D = -30\text{mA}$, $V_{GS} = -2.5\text{V}$		11	15.4	Ω
	$R_{DS(on)3}$	$I_D = -1\text{mA}$, $V_{GS} = -1.5\text{V}$		27	54	Ω
Input Capacitance	C_{iss}	$V_{DS} = -10\text{V}$, $f=1\text{MHz}$		7.5		pF
Output Capacitance	C_{oss}			5.7		pF
Reverse Transfer Capacitance	C_{rss}			1.8		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		24		ns
Rise Time	t_r			55		ns
Turn-OFF Delay Time	$t_d(off)$			120		ns
Fall Time	t_f			130		ns
Total Gate Charge	Q_g	$V_{DS} = -10\text{V}$, $V_{GS} = -10\text{V}$, $I_D = -100\text{mA}$		1.43		nC
Gate-to-Source Charge	Q_{gs}			0.18		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			0.25		nC
Diode Forward Voltage	V_{SD}	$I_S = -100\text{mA}$, $V_{GS}=0\text{V}$		-0.83	-1.2	V

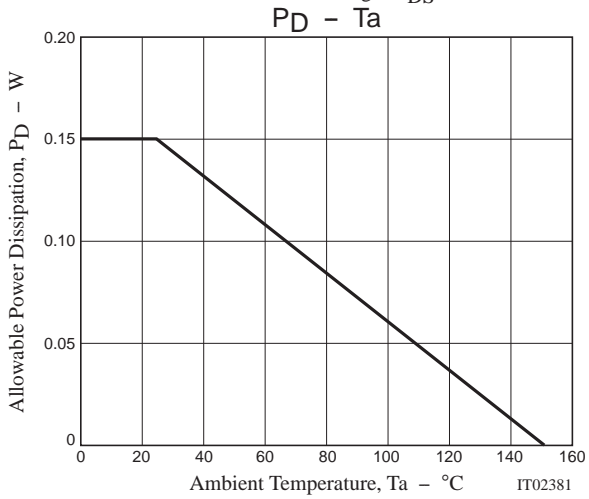
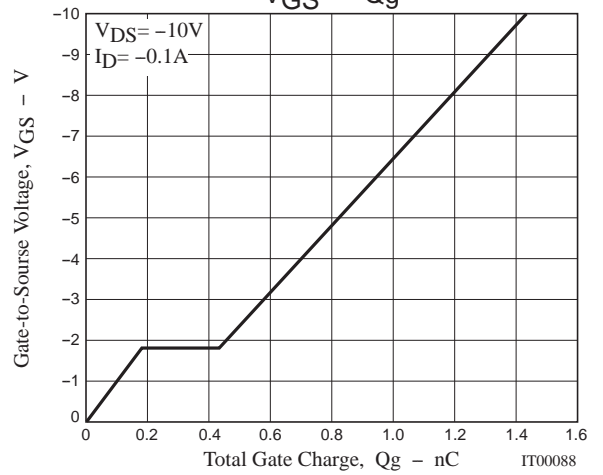
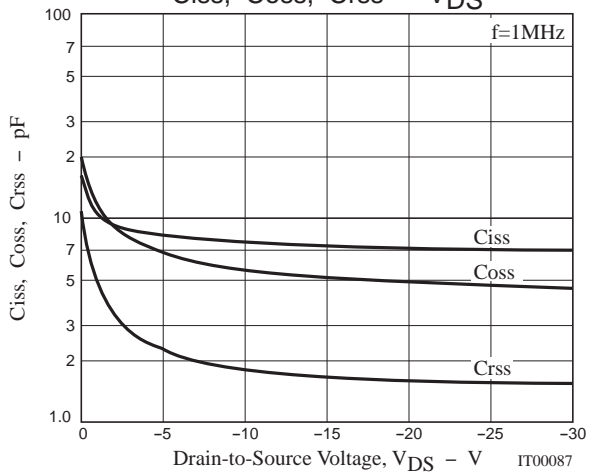
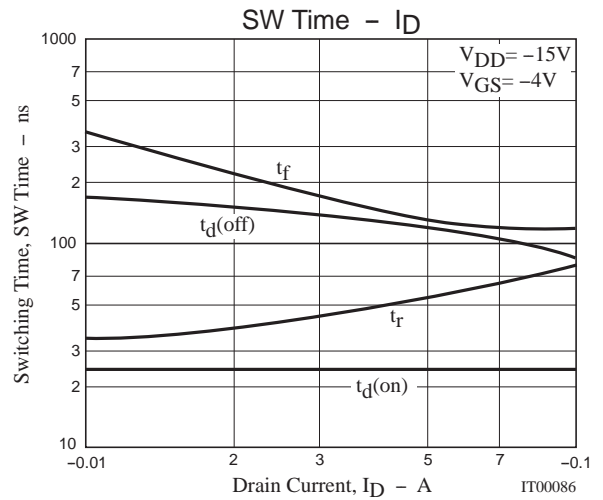
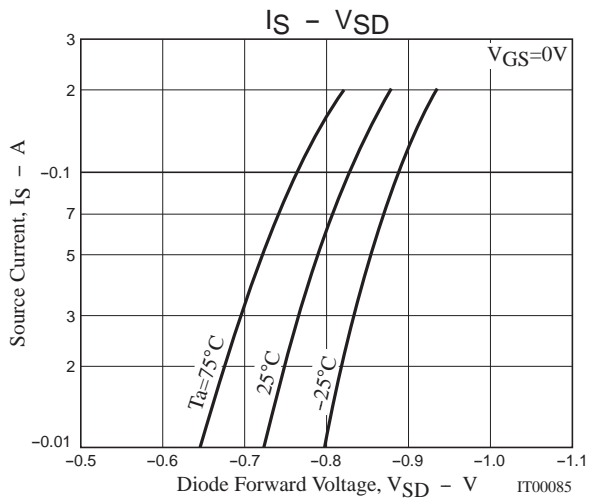
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
3LP01SS-TL-E	SSFP	8,000pcs./reel	Pb Free
3LP01SS-TL-H	SSFP	8,000pcs./reel	Pb Free and Halogen Free





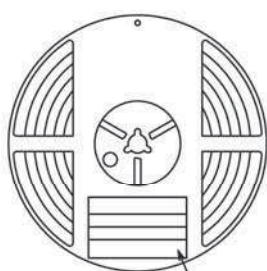
Embossed Taping Specification

3LP01SS-TL-E, 3LP01SS-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
SSFP	SSFP	8,000	40,000	240,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimension::mm (external) 440×195×210

Packing method



Reel label

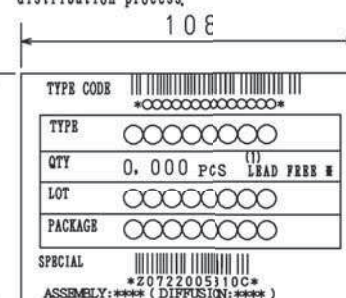
Reel label, Inner box label
(unit:mm)

Type No. →
LOT No. →
Quantity →
Origin →



Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical
distribution process.



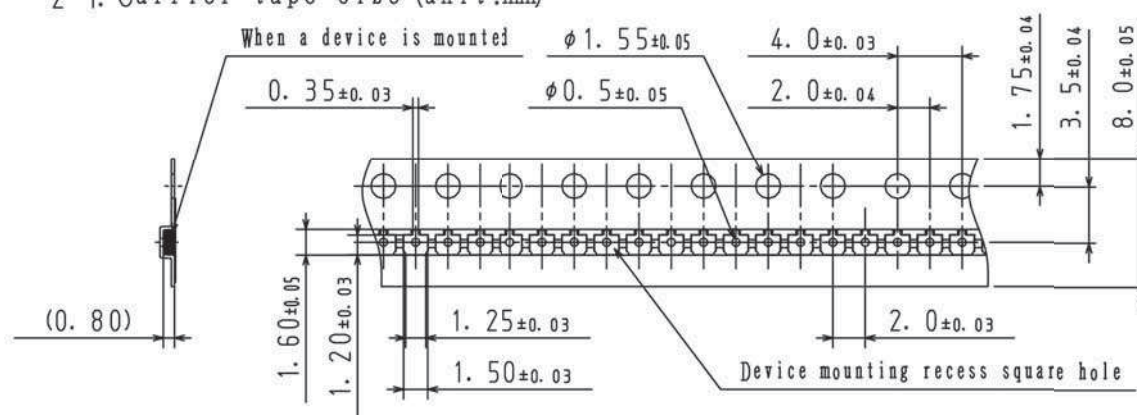
NOTE (1)

The LEAD FREE * description shows that the surface
treatment of the terminal is lead free.

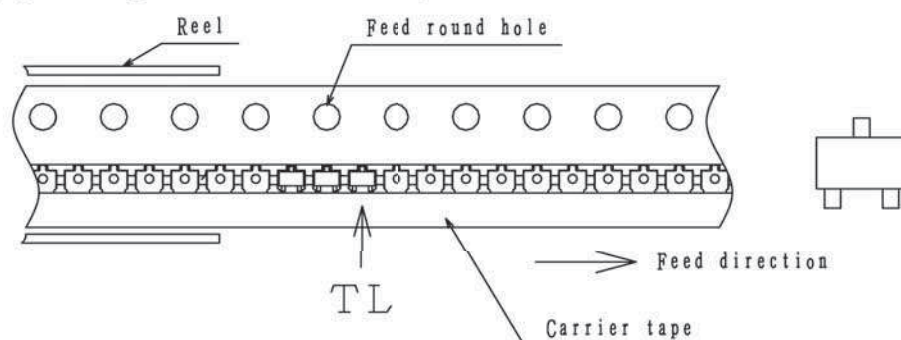
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

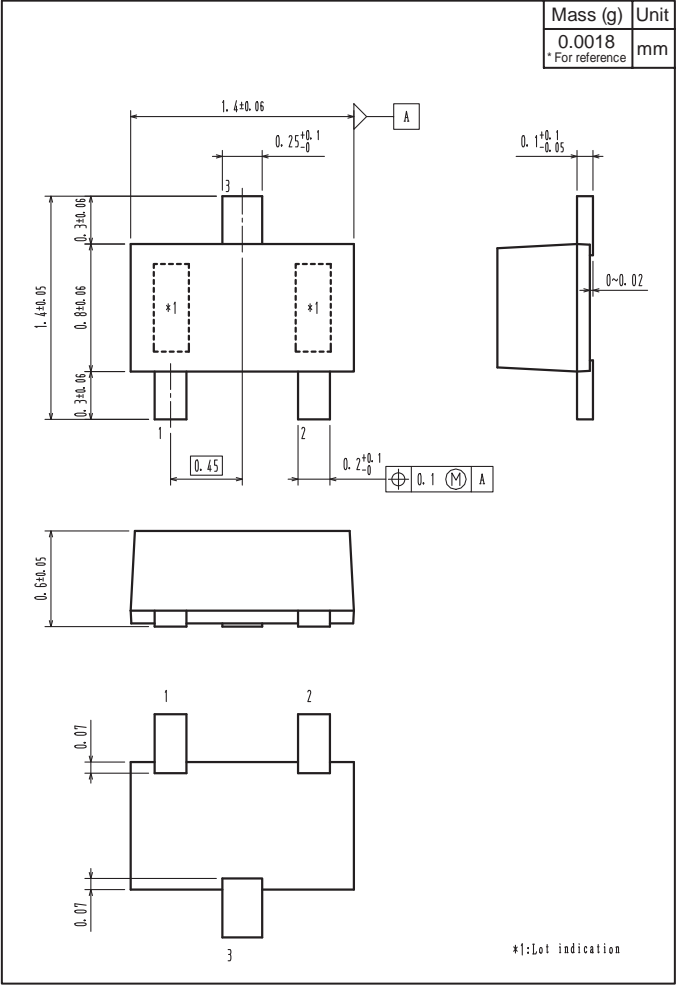


Those with pin 1 index on the feed hole side.....TL

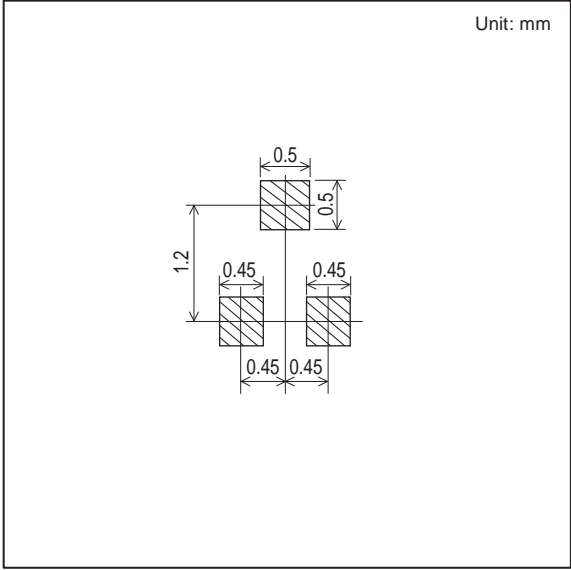
3LP01SS

Outline Drawing

3LP01SS-TL-E, 3LP01SS-TL-H



Land Pattern Example



Note on usage : Since the 3LP01SS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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